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Cadence Design Systems, Inc., 555 River Oaks Parkway, San Jose, CA 95134, USA

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About This Manual

This document provides information on new and changed features for version 5.8 of the Cadence[®] Library Exchange Format (LEF) and Design Exchange Format (DEF) integrated circuit description languages.

How This Document Is Organized

This What's New document is organized into the following chapters:

New Features

This chapter describes features that were added or changed since version 5.7 of LEF and DEF.

New features are those that introduce new functionality into LEF and DEF. Any enhancements made to existing statements to support a new feature are also described in this chapter.

Related Documents

The following documents provide detailed information about LEF and DEF, and the LEF and DEF application programming interfaces.

■ <u>LEF/DEF Language Reference</u>

About This Manual

New Features

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New Features

Overview

Multi-Mask Patterning Technology

The multi-mask patterning technology allows you to define multi-mask patterns for layers. You can define multi-mask statements that split a single layer into two or three masks. The syntax enhancements made to LEF/DEF v5.8 support more than three masks, though most applications support two or three masks only.

The subsequent sections describe the new syntax changes that have been made to incorporate this new feature.

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New LEF Features

The following sections describe the enhancements that have been made to support multimask patterning for LEF.

LEF Layers Support Masks

The MASK statement was added to specify how many masks for double- or triple-patterning will be used for a specified layer. You can use this statement for layers - cut, routing, implant, overlap, and/or masterslice.

Includes the following new syntax (in bold):

```
LAYER layerName

TYPE ROUTING; #or TYPE CUT, IMPLANT, MASTERSLICE, OVERLAP

[MASK numMasks;]
```

Fixed Masks for Layers and Macros

Some technologies do not allow mask shifting for cells using multi-mask patterning, e.g., pin and routing shapes are all pre-colored and must not be shifted to other masks. The FIXEDMASK statement was added to indicate that mask shifting is not allowed. All the LEF macro pin mask assignments are kept fixed and cannot be shifted to a different mask.

Includes the following new syntax (in bold):

```
For layers:
```

```
FIXEDMASK ;
  LAYER <statement>

For macros:
  MACRO macroName
     [CLASS className [subclassName] ;]
     [FIXEDMASK ;]
```

LEF Via Adds Masks for Fixed Vias

For fixed vias - rectangle or polygon - the masks in the via-master for cut layer are required for multi-cut vias. The VIARULE statement was enhanced to include masks. The MASK

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statement indicates which mask for double- or triple-patterning lithography is to be applied to the shapes defined using the RECT or POLYGON statements of the via master.

Includes the following new syntax (in bold):

```
VIA viaName [DEFAULT]
    { VIARULE viaRuleName ;
       CUTSIZE xSize vSize ;
       LAYERS botMetalLayer cutLayer topMetalLayer;
       CUTSPACING xCutSpacing yCutSpacing;
       ENCLOSURE xBotEnc yBotEnc xTopEnc yTopEnc;
       [ROWCOL numCutRows numCutCols;]
       [ORIGIN xOffset yOffset;]
        [OFFSET xBotOffset yBotOffset xTopOffset yTopOffset ;]
        [PATTERN cutPattern ;]
    | [RESISTANCE resistValue ;]
      {LAYER layerName;
       { RECT [MASK maskNum] pt pt;
        | POLYGON [MASK maskNum] pt pt pt ...; } ...
     } . . .
    [PROPERTY propName propVal ;] ...
END viaName
```

Macro Layer Geometries Support Masks

Macro layer geometries support multi-mask patterning. Three different masks can be added to the same layer geometries. The MASK statement was added to indicate which mask from double- or triple-patterning is to be used for path, rectangle, polygon, or via geometries.

```
{ LAYER layerName
        [EXCEPTPGNET]
        [SPACING minSpacing | DESIGNRULEWIDTH value];
    [WIDTH width ;]
        { PATH [MASK maskNum] pt ...;
        | PATH [MASK maskNum] ITERATE pt ... stepPattern;
        | RECT [MASK maskNum] pt pt;
        | RECT [MASK maskNum] ITERATE pt pt stepPattern;
        | POLYGON [MASK maskNum] pt pt pt pt ...;
        | POLYGON [MASK maskNum] ITERATE pt pt pt pt pt ... stepPattern;
```

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```
} ...
| VIA [MASK viaMaskNum] pt viaName;
| VIA ITERATE [MASK viaMaskNum] pt viaName stepPattern;
} ...
```

For syntax information, see <u>"LEF Syntax"</u> chapter in the *LEF/DEF Language Reference*.

New DEF Features

The following sections describe the enhancements that have been made to support multimask patterning for DEF.

Routing Blockages Add Mask Information

The BLOCKAGES section was enhanced to include masks. The MASK statement indicates which mask for double- or triple-patterning lithography is to be used for the specified shapes.

Includes the following new syntax (in bold):

Component Mask Shift Multi-Patterning Layers

The COMPONENTMASKSHIFT statement defines which layers of a component are allowed to be shifted from the original mask colors in the LEF. This can be useful to shift all the layers of a specific component in order to align the masks with other component or router mask settings to increase routing density. This definition allows a specific component to compactly describe the mask shifting for that component.

Includes the following new syntax:

```
[COMPONENTMASKSHIFT layer1 [layer2 ...];]
```

Components Adds Mask Shift Information

Some applications require the ability to "shift" the mask of pins and obstructions on a certain layer for a specific component to better align the pin masks with the routing masks.

The MASKSHIFT statement was added to allow shifting of the cell-master masks used in double- or triple-patterning for specific layers of an instance of the cell-master.

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Includes the following new syntax (in bold):

Fills Adds Masks

In order to support multi-patterning technologies up to three different masks for the same layer can be added.

The MASK statement was added to specify which mask for double- or triple-patterning lithography is to be applied to the specified rectangles, polygons, or via shapes on each layer.

Includes the following new syntax (in bold):

Nets Routing Points Enhancements

Nets Adds Rectangle and/or Virtual Connection

The NETS section was enhanced to provide the ability to create a rectangle or add a virtual connection to maintain the symbolic routing graph.

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The RECT statement allows creating a rectangle from the previous routing points. The VIRTUAL statement indicates that there is a virtual connection between the previous point and the new routing point.

Includes the following new syntax (in bold):

Nets Adds Masks

The NETS section routing points was enhanced to add masks - up to three different masks for the same layer can be added.

Includes the following new syntax (in bold):

```
{ ( x y [extValue] )
    [MASK maskNum] ( x y [extValue] )
    | [MASK viaMaskNum] viaName [orient]]
    | [MASK maskNum] RECT ( deltax1 deltay1 deltax2 deltay2 )
    | VIRTUAL ( x y ) } } ...
```

Special Nets Special Wiring Enhancements

To support multi-mask patterning up to three different masks for the same layers can be added to special nets.

A new VIA statement was added to make it more efficient to specify several power-vias.

Additionally, the route status - cover, fixed, routed, shield, and shape - can be applied to polygons, rectangles, and vias.

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[DO numX BY numY STEP stepX stepY]

DEF Via Adds Mask

} . . .

For fixed vias, rectangle or polygon, the masks in the via-master for cut-layer shapes are required for multi-cut vias. The MASK statement indicates which mask for double- or triple-patterning lithography is to be applied to the defined shapes.

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Tracks Adds Mask

The routing tracks can now have mask assignments to aid alignment of routing masks inside a block with the level above. The MASK statement indicates which mask for double- or triple-patterning lithography to use for the first routing track.

Includes the following new syntax (in bold):

Pins Adds Mask

The PINS syntax has been modified in include mask attributes. The MASK statement indicates which mask from double- or triple-patterning to use for pins or via shapes on each layer.

```
[PINS numPins ;
[ [- pinName + NET netName]
    [[+ PORT]
        [+ LAYER layerName
              [MASK maskNum]
              [SPACING minSpacing | DESIGNRULEWIDTH effectiveWidth]
                   pt pt
         | + POLYGON layerName
              [MASK maskNum]
              SPACING minSpacing | DESIGNRULEWIDTH effectiveWidth]
                   pt pt pt ...
         |+ VIA viaName
              [MASK viaMaskNum]
                   рt
         1 ...
         [+ COVER pt orient | FIXED pt orient | PLACED pt orient]
    1...
; ] ...
END PINS]
```

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Blockages Change Component, Pushdown, Exceptpgnet to be Independent And Not Exclusive

The BLOCKAGES section was enhanced to allow a blockage to simultaneously have COMPONENT, PUSHDOWN, and EXCEPTPGNET statements with the other attributes. These statements are now independent and not exclusive. The meaning of the keywords is unchanged.

Includes the following syntax changes (in bold):

```
[BLOCKAGES numBlockages;
[- LAYER layerName
    [+ SLOTS | + FILLS]
    [ + PUSHDOWN]
    [ + EXCEPTPGNET]
    [+ COMPONENT compName]
    [+ SPACING minSpacing | + DESIGNRULEWIDTH effectiveWidth]
    [+ MASK maskNum]
        {RECT pt pt | POLYGON pt pt pt ...} ...
;] ...
[- PLACEMENT
    [ + SOFT | + PARTIAL maxDensity]
    [ + PUSHDOWN]
    [+ COMPONENT compName]
        {RECT pt pt} ...
    ;] ...
END BLOCKAGES
```

For syntax information, see "DEF Syntax" chapter in the LEF/DEF Language Reference.